

## S-Band, GaN/SiC, RF Power Transistor

2.7 - 3.1 GHz | 180 W | 58% Efficiency typ | 12.6dB Gain typ | 50 V | 100µs Pulse Length, 10% Duty Cycle

IGN2731M180 and IGN2731M180S are high power GaN-on-SiC RF power transistors that have been designed to suit the unique needs of modern radar systems. They supply a minimum of 180W of peak output power, with typically 12.6dB of gain and 58% efficiency. They operate from a 50 V supply voltage. For optimal thermal efficiency, the transistors are housed in a metal-based package with an epoxy-sealed ceramic lid.

### FEATURES

- GaN on SiC HEMT Technology
- Output Power 180W
- Pre-matched Input and Output Impedances
- High Efficiency - 58% typical
- 100% RF Tested under 100µs, 10% duty cycle pulse conditions
- RoHS and REACH Compliant
- Full non-linear electrothermal model available, please contact the factory.

### APPLICATIONS

- S-band Radar Systems

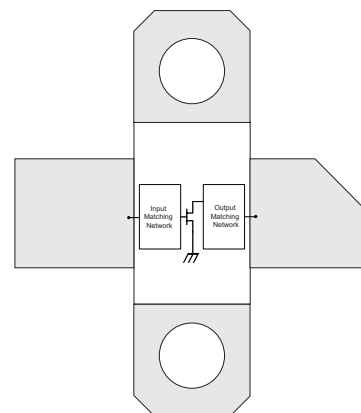


Table 1. Absolute Maximum Ratings (Not Simultaneous)

Parameter	Symbol	Value	Units	Test Conditions
DC Drain-Source Voltage	$V_{DS}$	140	V	25 °C
DC Gate-Source Voltage	$V_{GS}$	-8 to +1	V	25 °C
DC Drain Current	$I_D$	18	A	25 °C
DC Gate Current	$I_G$	18	mA	25 °C
RF Input Power	$P_{RFIN}$	13.3	W	25 °C
Operating Channel Temperature	$T_J$	-55 to +225	°C	
Storage Temperature	$T_{STG}$	-55 to +150	°C	
Soldering Temperature	$T_{SOLDER}$	260 for 10s	°C	

Note: Operation outside the limits given in this table may cause permanent damage to the transistor

Table 2. DC Electrical Characteristics (Case temperature = 25 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Gate Pinch-Off Voltage	$V_p$	-5.0			V	$V_{DS} = 50V, I_{DS} = 1mA$
Quiescent Gate Voltage	$V_Q$		-2.6		V	$V_{DS} = 50V, I_{DS} = 40mA$

**Table 3. RF Electrical Characteristics (Case temperature = 30 °C unless otherwise stated)**

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
RF Input Power	$P_{IN,RF}$	7.9	11.4	13.6	W	$P_{OUT} = 180W$ $f = 2.7, 2.9, 3.1 \text{ GHz}$ 100 $\mu$ s pulse length, 10% duty cycle $V_{DS} = 50V, I_{DS} = 40mA$
Gain	G	11.3	12.6	13.6	dB	
Drain Efficiency	$\eta$	50	58	75	%	
Pulse Droop	D	-0.5	-0.2	+0.3	dB	
Input Return Loss	IRL	10	12	18		
VSWR Mismatch Stability	VSWR-S	2:1				
VSWR Withstand	VSWR-LMT	3:1				

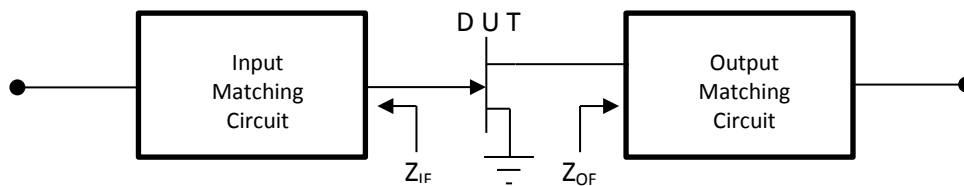
Note: Consult Integra Technologies Application Note 001 for information on how RF output power and pulse droop are measured.

**Table 4. Thermal Resistance (Case temperature = 30 °C unless otherwise stated)**

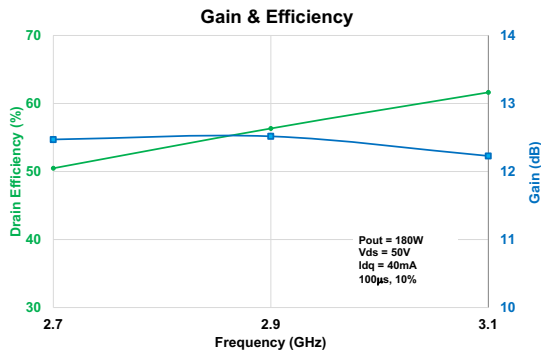
Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Peak Thermal Resistance, Channel to Case	$R_{TH}$		0.5		°C/W	$P_{dis} = 147.3W$ 100 $\mu$ s pulse length, 10% duty cycle $V_{DS} = 50V, I_{DS} = 40mA$

**Table 5. Matching Circuit Impedances (Case temperature = 25 °C unless otherwise stated)**

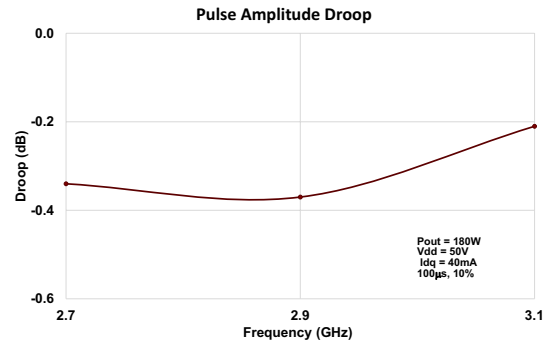
Frequency (GHz)	$Z_{IF}$	$Z_{OF}$	Units	Test Conditions
2.7	3.4 - j 5.7	3.5 - j 6.4	$\Omega$	$P_{OUT} = 180W$ 100 $\mu$ s Pulse length, 10% Duty Cycle $V_{DS} = 50V, I_{DS} = 40mA$
2.9	3.9 - j 4.5	3.5 - j 5.3	$\Omega$	
3.1	4.6 - j 4.3	3.6 - j 4.9	$\Omega$	



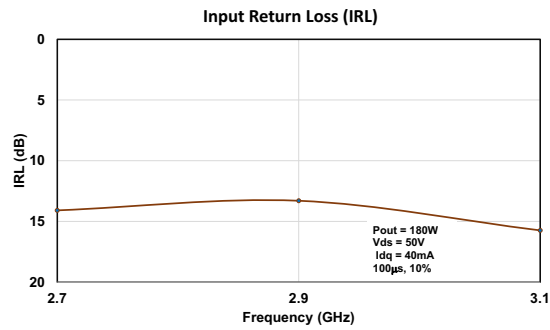
**TYPICAL PERFORMANCE**



**Figure 1**

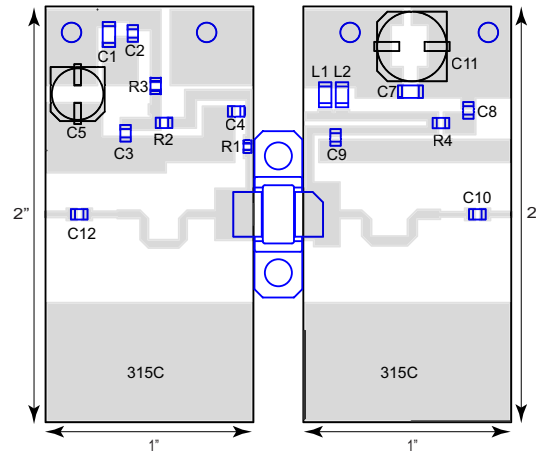


**Figure 2**



**Figure 3**

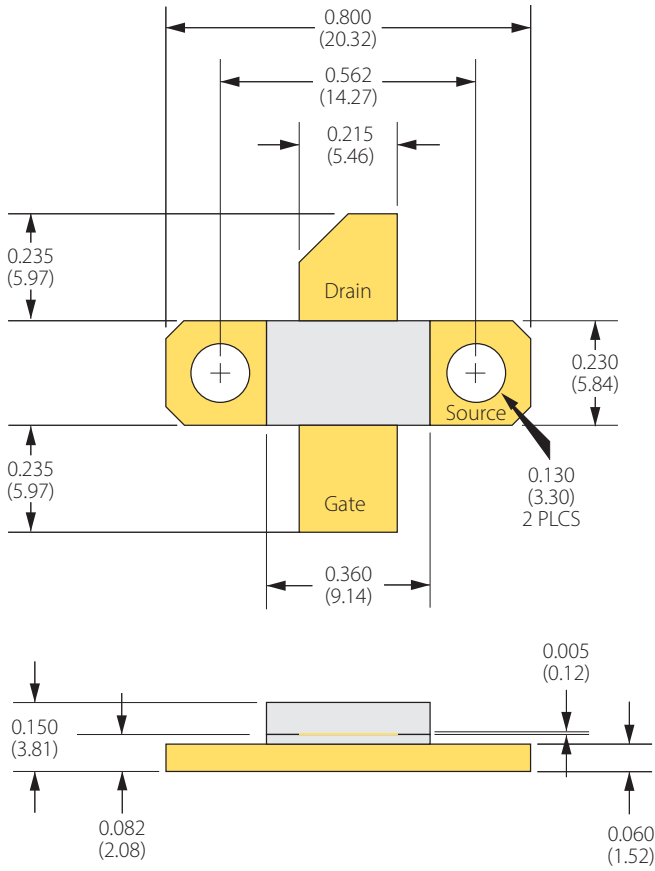
**TEST FIXTURE**



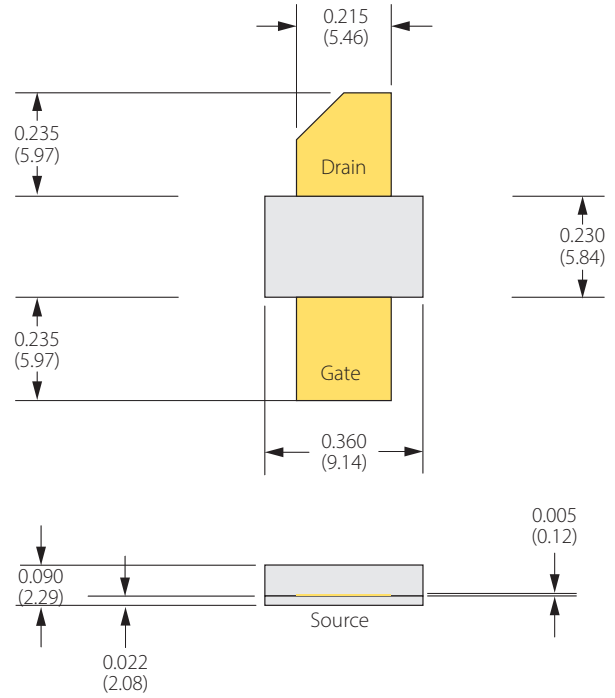
**Bill of Materials for IGN2731M180 Test Fixture**

Designator	Description	Quantity
C1, C7	CAP 1 $\mu$ F, 1206, 100V, X7R	2
C2, C3, C8	CAP 0.1 $\mu$ F, 0805, 100V	3
C4, C9	CAP 5.6pF, 0805, 250V	2
C5	CAP 47 $\mu$ F, 25V	1
C10, C12	CAP 12pF, 0805, 250V	2
C11	CAP 68 $\mu$ F, 63V, Electrolytic	1
L1, L2	IND FB, 33 OHM, 1205, 6A	2
R1	RES 10 OHM, 0603	1
R2	RES 100OHM, 0805	1
R3	RES 270 OHM, 0805	1
R4	RES 100 OHM, 0805	1
PC Board Type	ROGERS 25 mil, 1oz/1oz, Copper	2

**PACKAGE PL32A1**



**BOLT-DOWN FLANGE OPTION  
IGN2731M180**



**EARLESS FLANGE OPTION  
IGN2731M180S**

**Dimensions: Inches (mm)**

### ESD Rating

Parameter	Rating	Standard
ESD Human Body Model (HBM)	TBD	ESDA/JEDEC JS-001-2012
ESD Charged Device Model (CDM)	TBD	JEDEC JESD22-C101F
Moisture Sensitivity Level (MSL)	Unlimited Shelf Life	IPC/JEDEC J-STD-020

### RoHS Compliance

Integra Technologies, Inc declares that its GaN and LDMOS Transistor Products comply with EU Directive 2011/65/EU on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863/EU.

### REACH Compliance

Integra Technologies supports EU Regulation number 1907/2006 concerning the Registration, Evaluation, Authorization, and Restriction of Chemicals (REACH) as these apply to Integra semiconductor products, development tools, and shipping packaging.

In support of the REACH regulation, Integra will:

- Inform customers and recipients of Integra product if they contain any substances that are of very high concern (SVHC) per the European Chemical Agency (ECHA) website.
- Notify ECHA if any Integra product that contains any SVHCs which exceed guidelines for REACH chemicals by weight per part number and for total content weight per year for all products produced in or imported to the European market.
- Cease shipments of product containing REACH Annex XIV substances until authorization has been obtained.
- Cease shipment of product containing REACH Annex XVII chemicals when restrictions apply.

Integra has evaluated its materials, BOMs, and product specifications and product and has determined that this transistor conforms to all REACH and SVHC regulations and guidelines. Integra has implemented actions and control programs that will assure continued compliance.

### Disclaimer

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#### DEFINITIONS:

##### DATA SHEET STATUS

Advanced Specification - This data sheet contains Advanced specifications.

Preliminary Specification - This data sheet contains specifications based on preliminary measurements and data.

Final Specification - This data sheet contains final product specifications.

**MAXIMUM RATINGS** Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.

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